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PCN #: 126
Notification Date: 13 June 2005

Product / Process Change Notice

Parts Affected:
Chip process CP214, NPN RF transistors, wafers, and die in chip form.

Extent of Change:
Die size and die pattern change.
The CP214 chip process currently measures 16 x 16 mils and is being replaced by the CP229 chip process which measures 21.7 x 21.7 mils.

Reason for Change:
An alternate wafer foundry was approved for RF transistor technology.

Effect of Change:
The CP229 meets all electrical parameters of the 2N5109 as per Central's data sheet with the exception of the max h_{FE} limit. The h_{FE} limit @ V_{CE}=15V, I_C=50mA is being changed from 150 MAX to 210 MAX.

Qualification:
Standard evaluation and qualifications completed resulting in no electrical rejects.

Effective Date of Change:
Existing inventory will be shipped until depleted.

Sample Availability:
Please contact Salesperson or Manufacturer's Representative.

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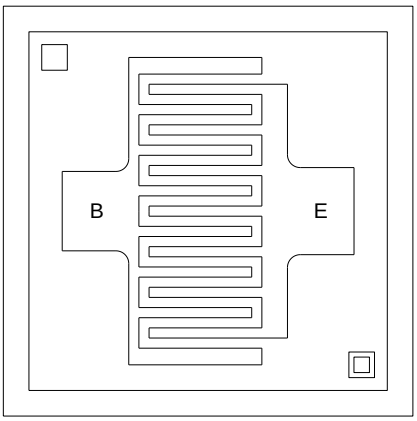
Figures:

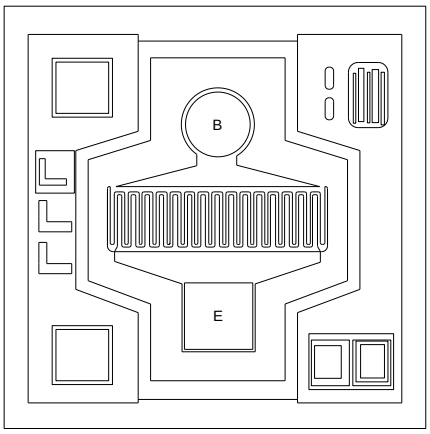
Figure 1: CP214 Chip Geometry



BACKSIDE COLLECTOR R1

Die Size:	16 x 16 mils
Die Thickness:	7.5 mils
Bond Pad Area (Emitter):	2.9 x 3.4 mils
Bond Pad Area (Base):	2.9 x 3.4 mils
Topside Metal:	Al (20,000Å)
Backside Metal:	Au (16,000Å)

Figure 2:CP229 Chip Geometry



BACKSIDE COLLECTOR R1

Die Size:	21.7 x 21.7 mils
Die Thickness:	8.7 mils
Bond Pad Area (Emitter):	3.4 x 3.4 mils
Bond Pad Area (Base):	3.2 mils diameter
Topside Metal:	Al (10,000Å)
Backside Metal:	Au (10,000Å)

Part Numbers Affected:

CP214-2N5109-CT
CP214-2N5109-WN
2N5109